

of barium atoms located on said surface of said substrate material.

22. A semiconductor device comprising:

a substrate;

or
cont' a barrier film comprised of a layer of elemental barium atoms on said substrate; and

a material on said barrier film.

23. A semiconductor device comprising:

a substrate;

a barrier film comprising barium atoms having a thickness less than 100Å on said substrate; and

a material on said barrier film. --

REMARKS

Prior to examination, applicants request that the Examiner enter the foregoing amendment to the claims. An early action on the merits is respectfully requested.

Respectfully submitted,

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